

# Model 40612

## Pyroelectric IR Detector with Internal JFET and Load/Feedback Resistor



Manufactured under one or more of the following U.S. patents: 3,839,640 - 4,218,620 - 4,326,663 - 4,384,207 - 4,437,003 - 4,441,023 - 4,523,095

**Model 40612** consists of a single lithium tantalate sensing element, JFET and high megohm resistor sealed into a 4-pin TO-5 transistor housing with an optical filter.

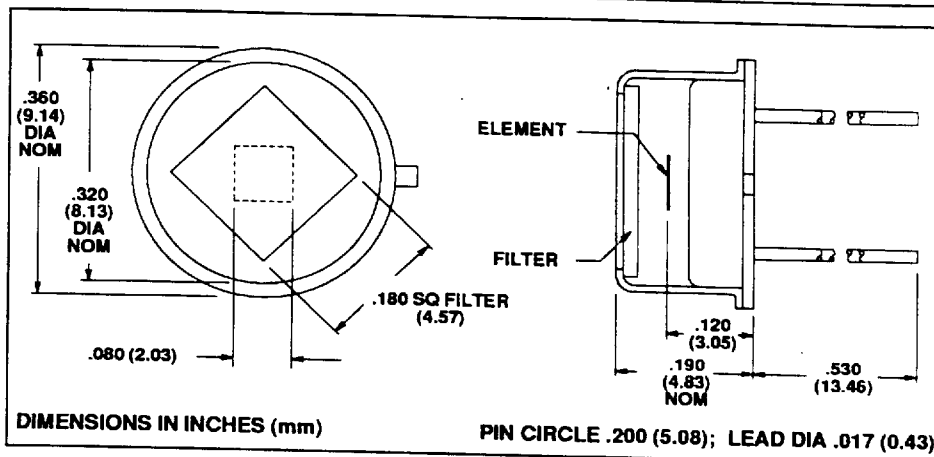
When compared to the Model 406, Model 40612 has a reduced low frequency response, allowing for excellent stability. It also features optimum signal-to-noise performance in the 1 - 10 Hz frequency range.

The electronics are configured so the detector can be operated in two ways: (1) As a pyroelectric detector with an integral source follower or (2) as a detector with a low noise, high impedance JFET to be used as the input to an external operational amplifier with the high megohm resistor used as the current-to-voltage feedback resistor.

An external source resistor is needed to set the drain current and consequently the operating parameters of the JFET. A 47 K $\Omega$  or greater value resistor is recommended.

### Applications

- Flame Detection
- Industrial Control
- Motion Sensing
- Gas Analysis
- Pyrometry
- Instrumentation
- Furnace Flame Control



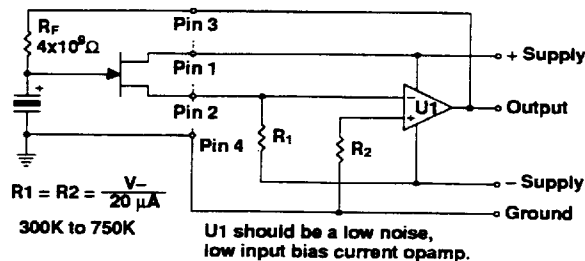
Characteristics	40612	Unit	Test Conditions	ELTECdata Reference
Detector Type:	Single	—		
Element Size:	2.0 x 2.0	mm	Nominal	
Optical Bandwidth:	0.1 to 1000	$\mu\text{m}$	Various Filters	101
Responsivity (Typ):	360	V/W	8 to 14 $\mu\text{m}$ @ 10Hz	
Noise (Typ):	15	$\mu\text{V}/\sqrt{\text{Hz}}$	1.0 Hz,	
(Max):	20		p-p (1 minute)	
NEP (Typ):	$2.0 \times 10^{-9}$	W/ $\sqrt{\text{Hz}}$	8 to 14 $\mu\text{m}$ , 10 Hz, BW 1 Hz	100
D* (Typ):	$8.5 \times 10^7$	$\text{cm}\sqrt{\text{Hz}}/\text{W}$	8 - 14 $\mu\text{m}$ , 10 Hz, BW 1 Hz	100
Operating Voltage (Min):	3	V	V+ to Gnd	104
(Max):	15			(4.1.c)
Operating Current (Min):	0.1	$\mu\text{A}$		104
(Max):	40			(4.1.c)
Offset Voltage (Min):	0.3	V	$R_S = 100\text{K}\Omega$	104
(Max):	1.2			Fig. 4
Output Impedance:	$\leq R_S$			
Thermal Breakpoint $f_T$ (Typ):	0.25	Hz		102
Electrical Breakpoint $f_e$ (Typ):	1.1	Hz	$R_L = 4 \times 10^9 \Omega$	102
Recommended Operating Temperature:	-40 +100	$^{\circ}\text{C}$		
Incident Power Limit: (Max):	10	mW		
Storage Temperature:	-55 +125	$^{\circ}\text{C}$	$\Delta T < 50 ^{\circ}\text{C}/\text{minute}$	

Characteristics (in Voltage Mode) at 25 $^{\circ}\text{C}$ , with -3 filter,  $V_D = 5 \text{ VDC}$ ,  $R_S = 100\text{K}\Omega$  unless otherwise stated.

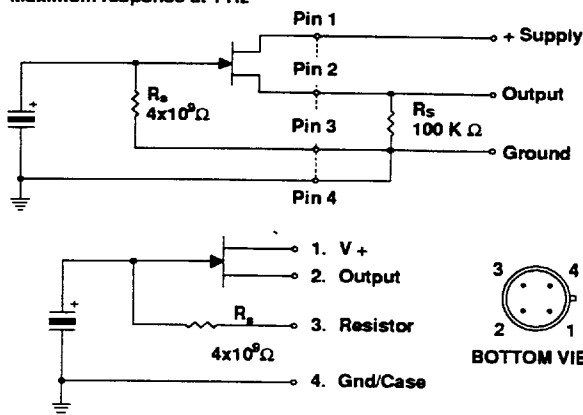
Data established on a sample basis and is believed to be representative.

**Power Supply:**  $\pm 6$  Volts to  $\pm 15$  Volts

- High Gain
- Flat Response from .5 to 100 Hz



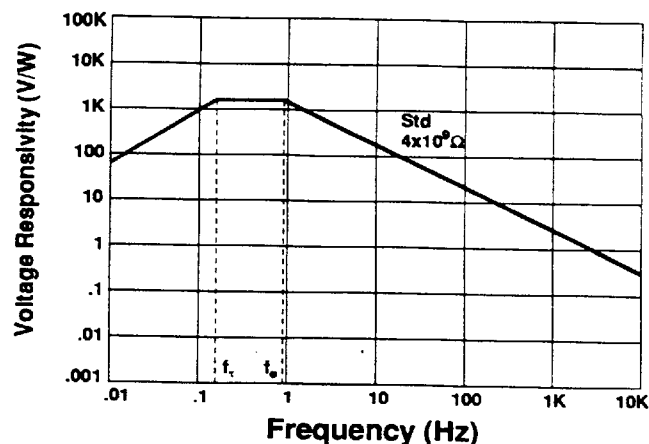
- Simple
- Lowest possible noise
- Maximum response at 1 Hz



**Optical Design:** Use of a detector with a filter in an optical system may require consideration of the image displacement toward the filter. This displacement ( $s$ ) caused by the insertion of a planoparallel plate (filter thickness =  $t$ ; refractive index =  $N$ ) is given by  $s = (t/N)(N-1)$ .

**Soldering:** Use minimum heat and a heat sink leads between case and solder points. Leave minimum lead length of .250 inch (6.35mm). DO NOT MACHINE SOLDER.

**Thermal Shock:** Temperature changes and rate of change must be kept to a minimum ( $<50^{\circ}\text{C}/\text{min.}$ ) to prevent damage.



The voltage response of this detector is dependent on the pulse rate or equivalent frequency of input.

- Radiated and conducted RF signals
- Subsequent amplification or signal conditioning stages
- Power supply noise
- Components, such as high value resistors and capacitors (tantalum and aluminum electrolytic)
- Mechanical contacts and poor solder joints
- Shock and vibration induced microphonics
- Outside thermal influences on the detector other than the desired infrared input, i.e. drafts, and radiation from nearby hot components

**All of these noise sources should be considered carefully when the information signal is <1mV for voltage mode operation and 20 mV for current mode operation.**

**Gate Protection:** Treat as static sensitive devices because voltages to 100 volts can be generated in the crystal by rapid temperature changes. If the internal resistor is not connected to some path to ground, the full voltage will be presented to the JFET gate with possible JFET failure. The electroded sensing crystal (a dielectric sandwich) can be regarded as a self-generating capacitor with an RC discharge time constant of greater than 5 minutes.

**Light Leakage:** Slight sensitivity to visible light leaking through the glass-to-metal seal on the base may be observed.



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